| L Number | Hits | Search Text | DB | Time stamp |
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| 145 | 7 | @ad<=20000719 and 'doped channel' and 'raised source/drain' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/13 13:46 |
| 146 | 15 | @ad<=20000719 and 'doped channel' and 'elevated' with 'source/drain' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/13 13:50 |
| 147 | 22 | @ad<=20000719 and 'punch through' with 'channel' and 'elevated' with 'source/drain' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/13 13:51 |
| 148 | 20 | @ad<=20000719 and 'punchthrough' with 'channel' and 'elevated' with 'source/drain' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/13 13:51 |
| 149 | 14 | @ad<=20000719 and 'punchthrough' with 'channel' and 'raised' with 'source/drain' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/13 13:51 |
| 150 | 85 | @ad<=20000719 and Gardner-Mark-I.in. and 'punchthrough' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/13 13:59 |
| 151 | 166 | @ad<=20000719 and 'invert' with ('sidewall' or 'spacer') | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/13 15:41 |
| 153 | 18 | @ad<=20000719 and 'inverted' adj1 'sidewall' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/13 14:14 |
| 154 | 34 | @ad<=20000719 and 'inverted' adj1 'spacer' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/13 14:12 |
| 155 | 29 | (@ad<=20000719 and (257/330-333).ccls.) and 'doped channel' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/13 14:26 |
| 157 | 44 | (@ad<=20000719 and (257/330-333).ccls.) and 'punchthrough' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/13 14:19 |
| 158 | 594 | @ad<=20000719 and (257/330).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/13 14:26 |
| 159 | 295 | @ad<=20000719 and (257/331).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/13 14:27 |
| 160 | 255 | @ad<=20000719 and (257/332).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/13 14:27 |

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| 161 | 159 | @ad<=20000719 and (257/333).ccls. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/05/13<br>14:27 |
| 162 | 267 | @ad<=20000719 and (438/300).ccls. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/05/13<br>14:27 |
| 163 | 63 | @ad<=20000719 and 'invert transistor' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/05/13<br>15:41 |
| - | 647 | (257/288).ccls. and @ad<=20000719 | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/10/17<br>11:13 |
| - | 77 | ((257/288).ccls. and @ad<=20000719) and silicide | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/21<br>13:36 |
| - | 1 | (((257/288).ccls. and @ad<=20000719) and silicide) and 'trench transistor' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/21<br>13:36 |
| - | 256 | @ad<=20000719 and 'silicide' and 'gate' with 'spacer' with 'trench' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/22<br>09:33 |
| - | 2 | ("6201278").PN. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/21<br>13:53 |
| - | 54 | (438/259).ccls. and @ad<=20000719 and 'silicide' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/22<br>09:42 |
| - | 409 | @ad<=20000719 and 'miniaturize' with 'transistor' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/22<br>09:22 |
| - | 574 | @ad<=20000719 and 'miniaturize' with 'transistor' or 'semiconductor' and 'raised source/drain' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/10/17<br>12:33 |
| - | 0 | @ad<=20000719 and 'invert sidewall' and 'raised source/drain' and 'STI' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/10/17<br>12:35 |
| - | 6 | @ad<=20000719 and 'inverted' with 'spacers' and 'raised source/drain' and 'STI' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/10/17<br>12:43 |
| - | 3 | @ad<=20000719 and 'silicide' and 'gate' with 'spacer' with 'trench' and 'STI' and 'raised source/drain' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/10/17<br>12:33 |

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|---|---|---|---|---|---|---|
| — | | | 135 | (438/270).ccls. and @ad<=20000719 and 'silicide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/11/04 10:36 |
| — | | | 94 | (257/330).ccls. and @ad<=20000719 and 'silicide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/11/04 10:36 |
| — | | | 6 | @ad<=20000719 and 'doped channel' and 'raised source/drain' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/04 13:29 |
| — | | | 966 | @ad<=20000719 and (257/330-333).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/17 12:44 |
| — | | | 28 | (@ad<=20000719 and (257/330-333).ccls.) and 'doped channel' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/17 12:10 |
| — | | | 139 | (438/270).ccls. and @ad<=20000719 and 'silicide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/11/04 10:51 |
| — | | | 97 | (257/330).ccls. and @ad<=20000719 and 'silicide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/11/04 10:36 |
| — | | | 984 | @ad<=20000719 and (257/408).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/11/04 10:38 |
| — | | | 3231 | @ad<=20000719 and (438/300-305).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/13 14:27 |
| — | | | 84 | @ad<=20000719 and (438/242).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/17 12:46 |
| — | | | 187 | @ad<=20000719 and (438/259).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/04 15:36 |
| — | | | 73 | @ad<=20000719 and (438/376).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/11/04 10:57 |
| — | | | 1 | ((438/270).ccls. and @ad<=20000719 and 'silicide' ) and 'elevated source' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/11/04 10:51 |
| — | | | 0 | ((257/330).ccls. and @ad<=20000719 and 'silicide' ) and 'elevated source/drain' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/11/04 10:52 |

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| – | | | 202 | @ad<=20000719 and 'elevated source/drain' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/11/04 11:09 |
| | | | 2 | "20020072184" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/11/04 11:02 |
| – | | | 4 | @ad<=20000719 and 'elevated source/drain' and inverted adj1 'spacer' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/11/04 11:13 |
| – | | | 2 | ("5434093").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/11/04 11:12 |
| – | | | 9 | @ad<=20000719 and 'raised source/drain' and inverted adj1 spacer | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/04 13:39 |
| – | | | 2 | "20020072184" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/04 12:54 |
| – | | | 6 | @ad<=20000719 and 'doped channel' and 'raised source/drain' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/17 11:52 |
| – | | | 6 | @ad<=20000719 and 'doped channel' and 'raised source drain' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/04 13:30 |
| – | | | 11 | @ad<=20000719 and 'IGFET' with 'doped channel' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/04 13:36 |
| – | | | 0 | @ad<=20000719 and 'silicide gate' with 'doped channel' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/04 13:36 |
| – | | | 13 | @ad<=20000719 and 'silicide gate' and 'doped channel' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/04 13:38 |
| – | | | 2 | ("6197668").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/04 13:38 |
| – | | | 3 | @ad<=20000719 and gardner-mark.in. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/04 13:41 |
| – | | | 3 | gardner-mark.in. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/04 13:40 |

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| — | | 0 | @ad<=20000719 and Mark-Gardner.in. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/06/04<br>13:42 |
| — | | 525 | @ad<=20000719 and Gardner-Mark-I.in. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/06/04<br>14:10 |
| — | | 52 | @ad<=20000719 and Gardner-Mark-I.in. and 'punch' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/05/13<br>13:59 |
| — | | 108 | @ad<=20000719 and trench adj1 gate and 'punch' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/10/17<br>12:35 |
| — | | 28 | (@ad<=20000719 and (257/330-333).ccls.) and 'doped channel' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/05/13<br>14:18 |
| — | | 993 | (@ad<=20000719 and (257/330-333).ccls.) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/06/04<br>14:33 |
| — | | 145 | (@ad<=20000719 and (257/334).ccls.) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/06/04<br>15:03 |
| — | | 9 | (("6413823") or ("6406957") or ("6025232") or ("6472260")).PN. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/06/04<br>15:04 |
| — | | 1688 | @ad<=20000719 and (438/270-271).ccls. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/06/04<br>15:38 |
| — | | 2 | "20020072184" | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/10/17<br>11:14 |
| — | | 6 | @ad<=20000719 and 'doped channel' and 'raised source/drain' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/05/13<br>13:46 |
| — | | 28 | (@ad<=20000719 and (257/330-333).ccls.) and 'doped channel' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/10/17<br>12:11 |
| — | | 52 | @ad<=20000719 and Gardner-Mark-I.in. and 'punch' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/10/17<br>12:23 |
| — | | 0 | @ad<=20000719 and 'miniaturize' with 'transistor' and 'semiconductor' and 'raised source/drain' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/10/17<br>12:33 |

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| – | | 0 | @ad<=20000719 and 'miniaturize' with 'transistor' and 'raised source/drain' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/17 12:33 |
| – | | 5 | @ad<=20000719 and 'silicide' and 'gate' with 'spacer' with 'trench' and 'STI' and 'raised source' with 'drain' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/17 12:34 |
| – | | 108 | @ad<=20000719 and trench adj1 gate and 'punch' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/17 12:35 |
| – | | 1 | @ad<=20000719 and 'invert sidewall' and 'STI' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/13 14:10 |
| – | | 7 | @ad<=20000719 and 'inverted' with 'spacers' and 'raised source/drain' and 'STI' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/17 12:43 |
| – | | 589 | @ad<=20000719 and (257/330).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/17 12:56 |
| – | | 293 | @ad<=20000719 and (257/331).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/17 12:45 |
| – | | 253 | @ad<=20000719 and (257/332).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/17 12:45 |
| – | | 156 | @ad<=20000719 and (257/333).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/17 12:45 |
| – | | 1397 | @ad<=20000719 and (438/270).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/17 12:47 |
| – | | 193 | @ad<=20000719 and (438/259).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/17 12:49 |
| – | | 86 | @ad<=20000719 and (438/242).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/17 12:49 |
| – | | 90 | @ad<=20000719 and 'IGFET' same 'trench' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/17 12:56 |

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